

The role of solitons on the properties of electron transport through DNA-based transistor- a Green's function approach

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Abstract: In this work, we present a theoretical study of the conductance properties of molecular transistor model. The model considered has Metal/DNA/Metal structure.

Using a tight-binding Hamiltonian model [1] and the method based on generalized Green's function theory [2,3] with the Lowdin partitioning technique [4] and also Peyrard-Bishop model for describing the soliton in DNA [5,6], we investigate the role of the soliton in DNA electronic states (Fig.1) and in the I-V characteristics (Fig.2) of the Metal/DNA/Metal transistor. Our results show that in the presence of a distribution of solitons the band structure changes greatly and soliton states are created within the gap. In addition the voltage drop along the molecule give rise to a significant enhancement in the conductance. Also we study the effect of Metal/DNA coupling strength (Fig.3) and the length of the DNA molecule (Fig.4) on electronic state of the Metal/DNA/Metal transistor.

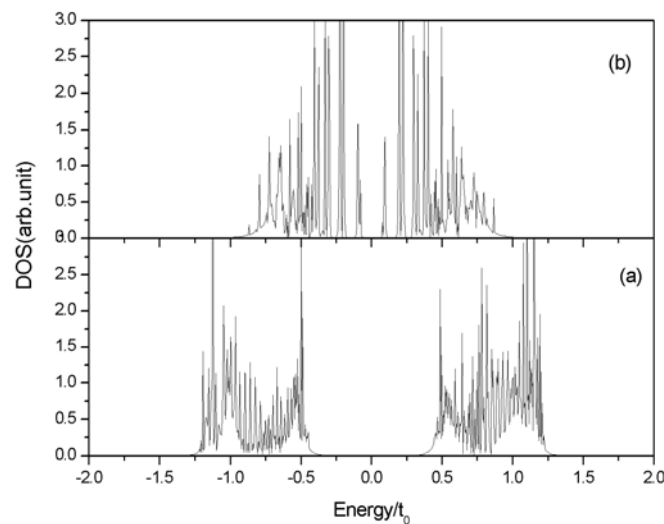


Figure1: Electronic Density of State (DOS), (a) in the absence and, (b) in the presence of solitons for 30 base-pairs in Metal/DNA/Metal Transistor.

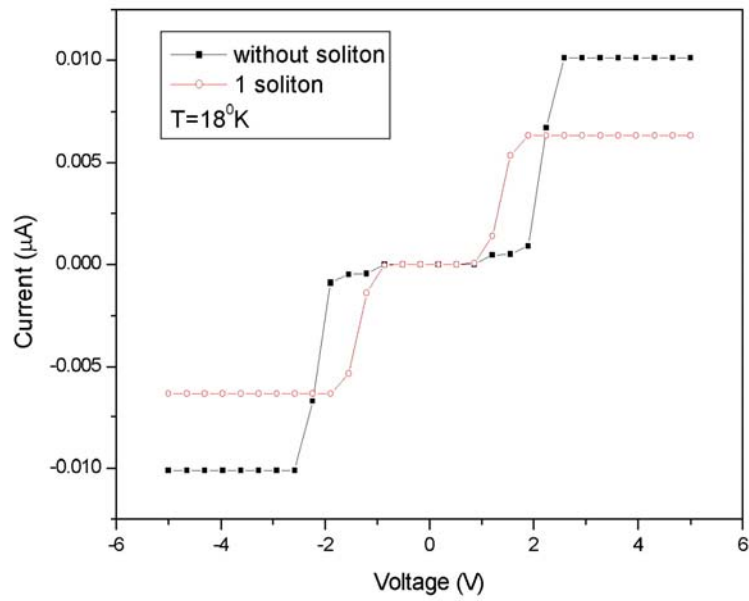


Figure 2: Approximate I-V Characteristics of Metal/DNA/Metal transistor in the absence and presence of soliton.

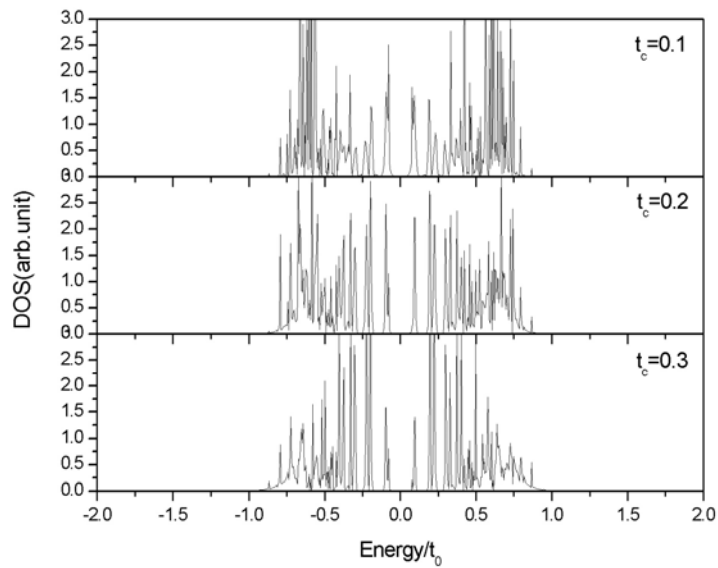


Figure 3: Density of states (DOS) for different amount of t_c in the presence of solitons for 30 base-pairs in the Metal/DNA/Metal transistor.

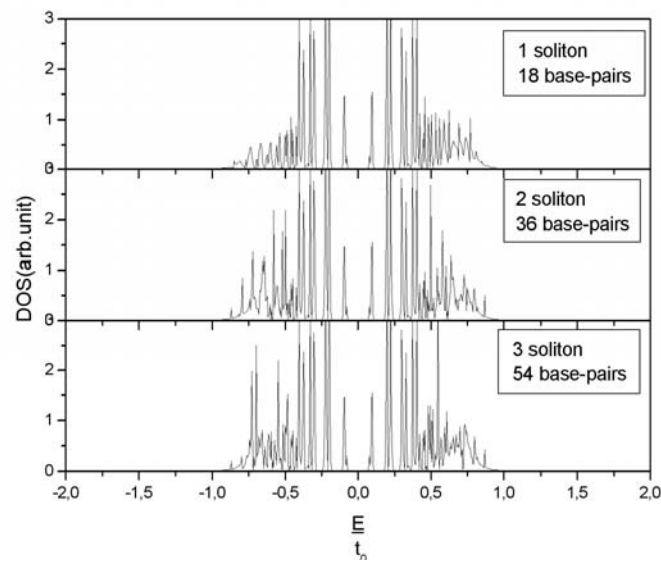


Figure 4: Density of state(DOS) for different number of solitons and base-pairs in the Metal/DNA/Metal transistor.

References:

- [1] D.Klotsa, R.A.Romer, M.S.Turner, *Bio. Phys. J.* **89**, 2187, 2005, "Electronic Transport in DNA"
- [2] V.Mujica, M.Kemp, M.A.Ratner, *J.Chem.Phys.* **101**, 6849, 1994, "Electron Conduction in Molecular Wires.I.A Scattering Formalism"
- [3] V.Mujica, M.Kemp, M.A.Ratner, *J.Chem.Phys.* **101**, 6856, 1994, " Electron Conduction in Molecular Wires.II.Application to Scanning Tunneling Microscopy"
- [4] P.O.Lowdin, *J. Mol. Spectrosc* **10**, 12, 1963, " Studies in Perturbation Theory"
- [5] M.Peyrard, A.R.Bishop, *Phys.Rev.Lett.* **62**, 2755, 1989, " Statistical Mechanics of a Nonlinear Model for DNA Denaturation"
- [6] M.Techera, L.L.Daemen, E.W.Prohofsky, *Phys.Rev. A* **40**, 6636, 1989, "Nonlinear Model of the DNA Molecule"